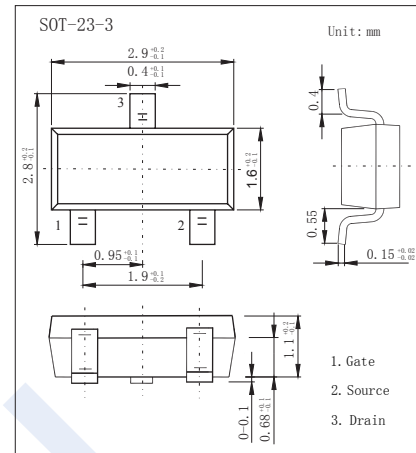
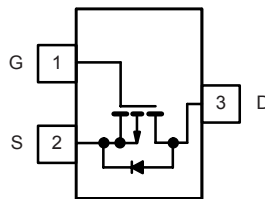


P-Channel MOSFET

SI2343DS (KI2343DS)

■ Features

- $V_{DS} (V) = -30V$
- $I_D = -4 A (V_{GS} = -10V)$
- $R_{DS(ON)} < 53m\Omega (V_{GS} = -10V)$
- $R_{DS(ON)} < 86m\Omega (V_{GS} = -4.5V)$



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	5 s	Steady State	Unit
Drain-Source Voltage	V_{DS}		-30	V
Gate-Source Voltage	V_{GS}		± 20	
Continuous Drain Current	I_D	$T_A = 25^\circ C$	-4	A
		$T_A = 70^\circ C$	-3.2	
Pulsed Drain Current	I_{DM}		-15	
Power Dissipation	P_D	$T_A = 25^\circ C$	1.25	W
		$T_A = 70^\circ C$	0.8	
Thermal Resistance.Junction- to-Ambient	R_{thJA}	100	166	$^\circ C/W$
Thermal Resistance.Junction- to-Foot	R_{thJF}		50	
Junction Temperature	T_J		150	$^\circ C$
Junction Storage Temperature Range	T_{stg}		-55 to 150	

P-Channel MOSFET

SI2343DS (KI2343DS)

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V _{DSS}	I _D =-250 μ A, V _{GS} =0V	-30			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-24V, V _{GS} =0V			-1	μA
		V _{DS} =-24V, V _{GS} =0V, T _J =55°C			-10	
Gate-Body leakage current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} I _D =-250 μ A	-1		-3	V
Static Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =-10V, I _D =-4A (Note.1)			53	mΩ
		V _{GS} =-4.5V, I _D =-3.1A (Note.1)			86	
On state drain current	I _{D(on)}	V _{GS} =-5V, V _{DS} =-10V (Note.1)	-15			A
Forward Transconductance	g _{FS}	V _{DS} =-5V, I _D =-4A (Note.1)		10		S
Input Capacitance	C _{iss}	V _{GS} =0V, V _{DS} =-15V, f=1MHz		540		pF
Output Capacitance	C _{oss}			131		
Reverse Transfer Capacitance	C _{rss}			105		
Total Gate Charge	Q _g	V _{GS} =-10V, V _{DS} =-15V, I _D =-4A		14	21	nC
Gate Source Charge	Q _{gs}			1.9		
Gate Drain Charge	Q _{gd}			3.7		
Turn-On DelayTime	t _{d(on)}	V _{DD} = - 15 V, R _L = 15 Ω I _D = - 1A, V _{GEN} = - 10 V R _G = 6 Ω		10	15	ns
Turn-On Rise Time	t _r			15	25	
Turn-Off DelayTime	t _{d(off)}			31	50	
Turn-Off Fall Time	t _f			20	30	
Maximum Body-Diode Continuous Current	I _S				-1	A
Diode Forward Voltage	V _{SD}	I _S =-1A, V _{GS} =0V			-1.2	V

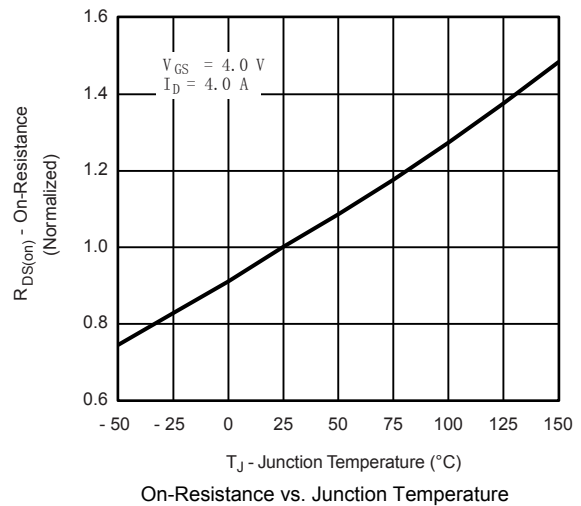
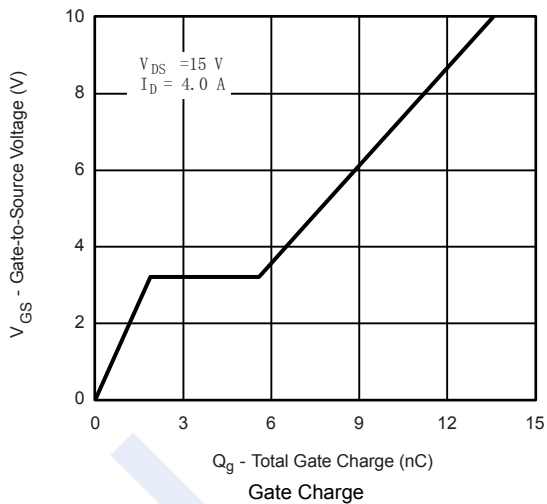
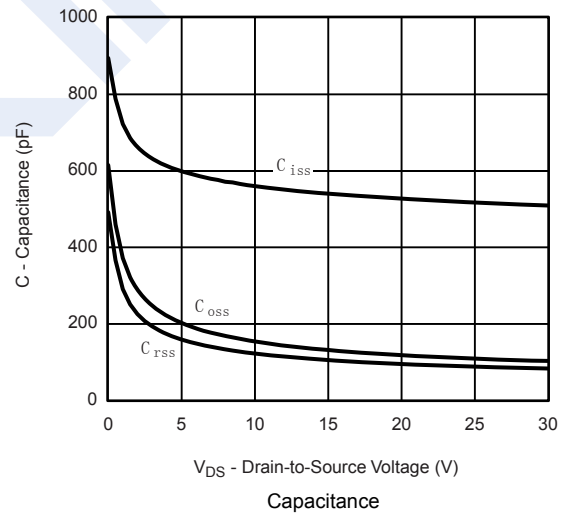
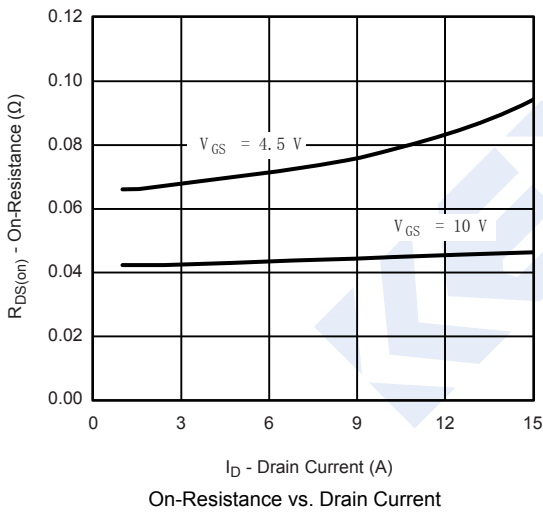
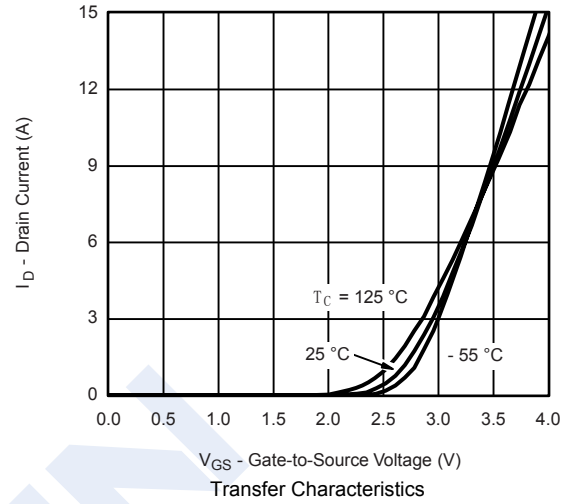
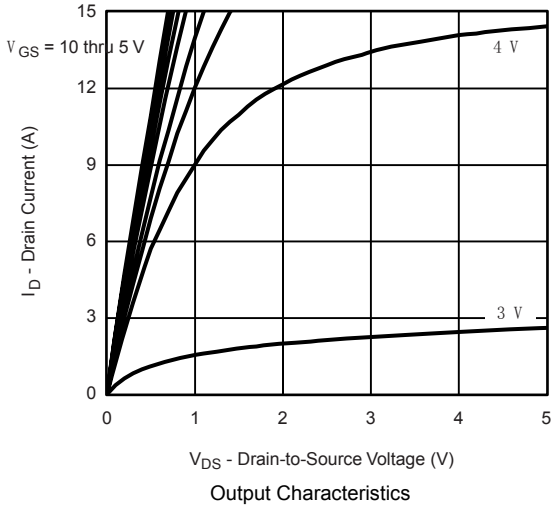
Note.1: Pulse test: PW ≤ 300 μs, duty cycle ≤ 2 %.

■ Marking

Marking	F3
---------	----

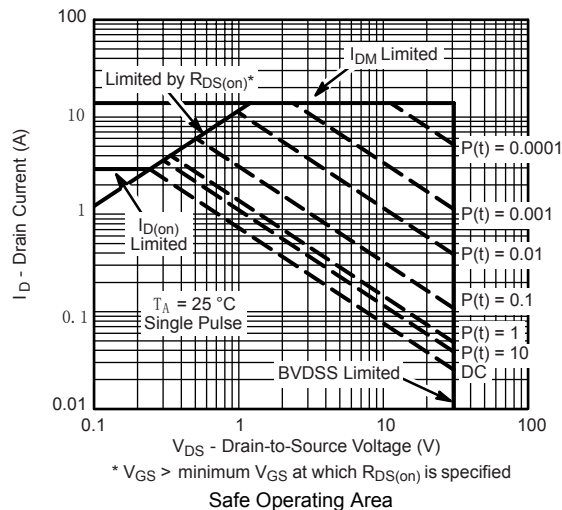
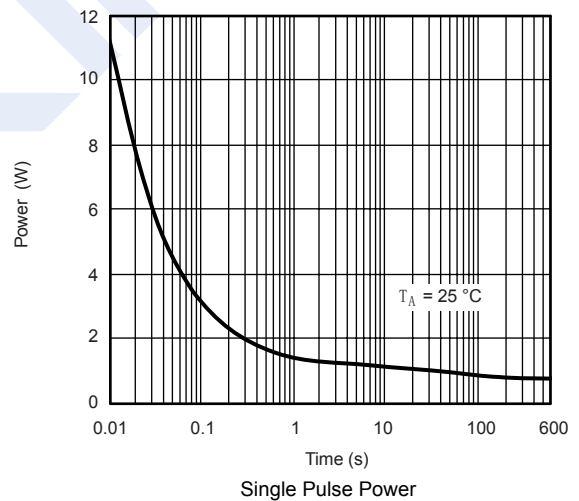
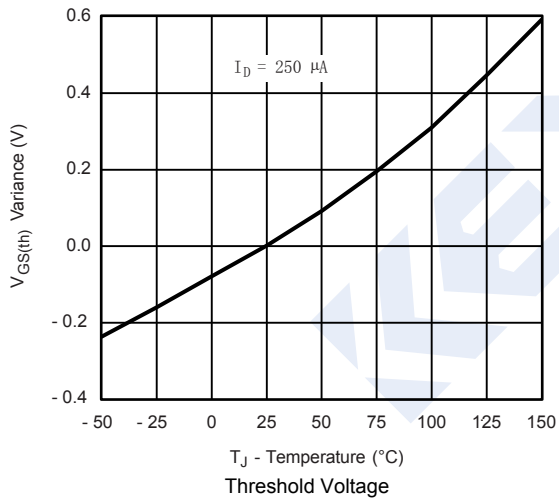
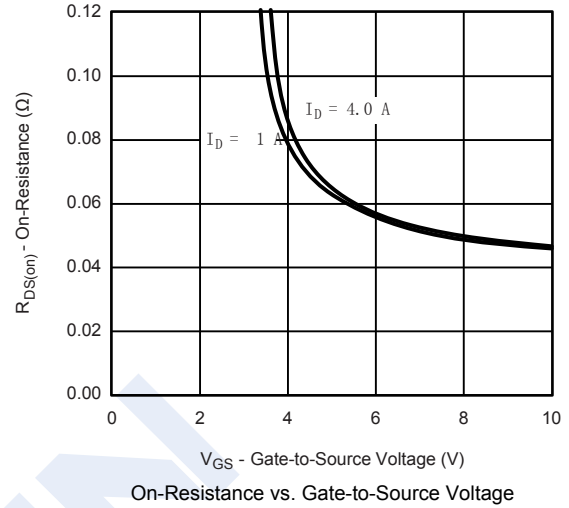
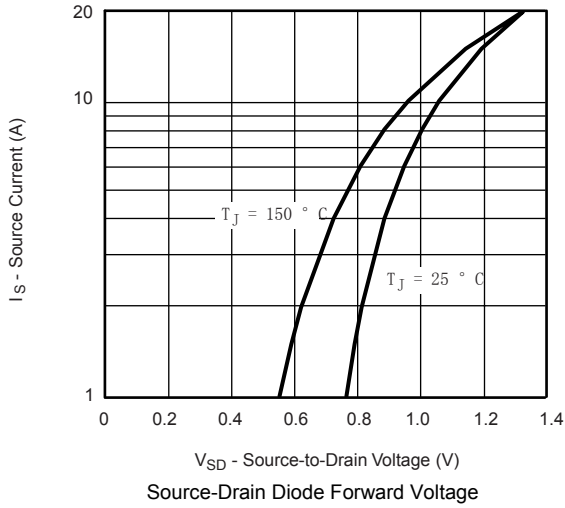
P-Channel MOSFET SI2343DS (KI2343DS)

Typical Characteristics



P-Channel MOSFET SI2343DS (KI2343DS)

Typical Characteristics



P-Channel MOSFET

SI2343DS (KI2343DS)

■ Typical Characteristics

